



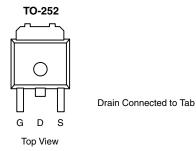
# N-Channel 60 V (D-S), 175 °C MOSFET, Logic Level

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A) <sup>a</sup>			
60	0.0093 at V <sub>GS</sub> = 10 V	50			
	0.0122 at V <sub>GS</sub> = 4.5 V	50			

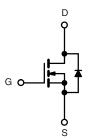
### **FEATURES**

- 175 °C Junction Temperature
- TrenchFET® Power MOSFET
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912





Ordering Information: SUD50N06-09L-E3 (Lead (Pb)-free)



N-Channel MOSFET

Parameter		Symbol	Limit	Unit	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Dunin Courset /T 475 900h	T <sub>C</sub> = 25 °C	,	50		
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 100 °C	ID	50 <sup>a</sup>		
Pulsed Drain Current	I <sub>DM</sub>	100	А		
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	50 <sup>a</sup>			
Avalanche Current	I <sub>AS</sub>	50			
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E <sub>AS</sub>	125	mJ	
Maximum Daway Dissination	T <sub>C</sub> = 25 °C	В	136	W	
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3 <sup>b</sup> , 8.3 <sup>b, c</sup>	] vv	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Manimum Innation to Ameliand	t ≤ 10 sec	R <sub>thJA</sub>	15	18	°C/W		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	' ¹thJA	40	50			
Maximum Junction-to-Case		R <sub>thJC</sub>	0.85	1.1			

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c.  $t \le 10$  s.

# SUD50N06-09L

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<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static			L		<u> </u>		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	2	3	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	μΑ	
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250		
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	50			Α	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.0074	0.0093		
5	В	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C			0.0160	Ω	
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C			0.0200		
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 15 A			0.0122		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A				S	
Dynamic	•						
Input Capacitance	C <sub>iss</sub>			2650			
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		470		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			225			
Total Gate Charge <sup>c</sup>	$Q_g$			47	70		
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		10		nC	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			12			
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			10	20		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 30 \text{ V, R}_{L} = 0.6 \Omega$		15	25	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		35	50		
Fall Time <sup>c</sup>	t <sub>f</sub>			20	30		
Source-Drain Diode Ratings and Cha	aracteristics (	T <sub>C</sub> = 25 °C)					
Pulsed Current	I <sub>SM</sub>				100	Α	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		1	1.5	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20 A, di/dt = 100 A/μs		45	100	ns	

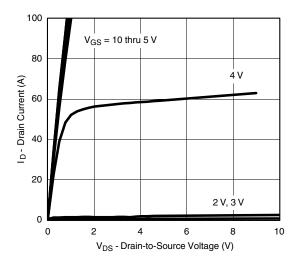
### Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. Independent of operating temperature.

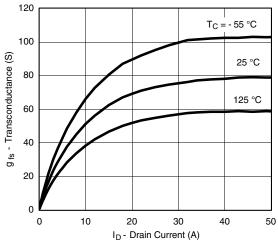
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



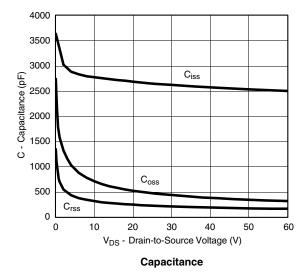
### TYPICAL CHARACTERISTICS (25 °C unless noted)

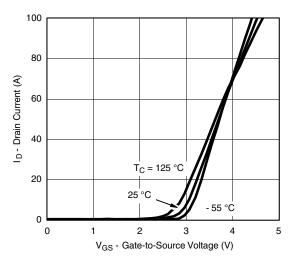


### **Output Characteristics**

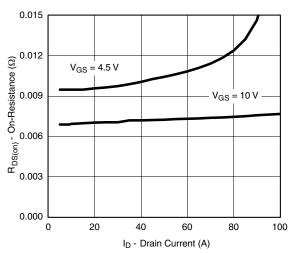


#### **Transconductance**

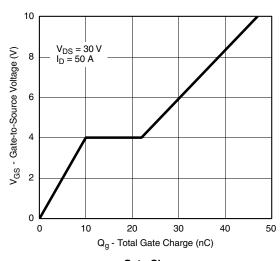




### **Transfer Characteristics**

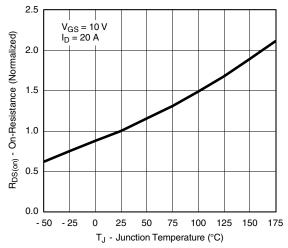


#### **On-Resistance vs. Drain Current**

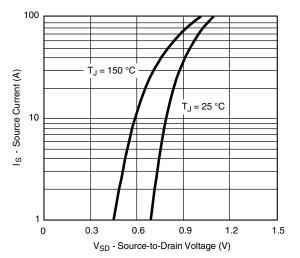


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## TYPICAL CHARACTERISTICS (25 °C unless noted)



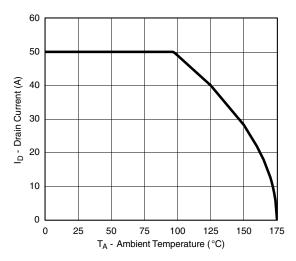
On-Resistance vs. Junction Temperature

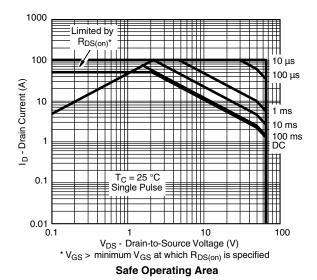


Source-Drain Diode Forward Voltage

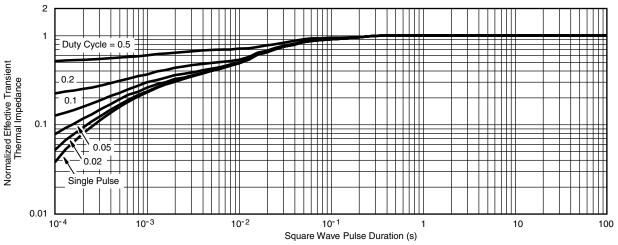


### THERMAL RATINGS





**Maximum Drain Current vs. Ambient Temperature** 



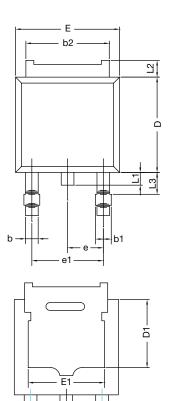
Normalized Thermal Transient Impedance, Junction-to-Case

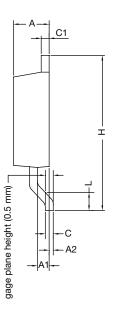
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### **TO-252AA CASE OUTLINE**





	MILLIMETERS		INC	INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28	2.28 BSC		BSC	
e1	4.57	BSC 0.180 B		3SC	
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

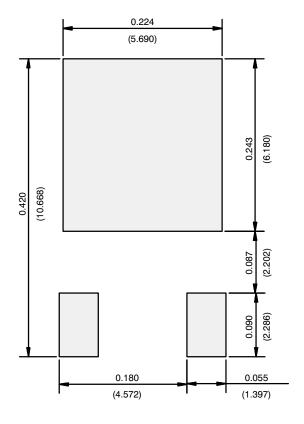
#### Note

• Dimension L3 is for reference only.

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## **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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